

Title (en)
THIN FILM TRANSISTORS AND THEIR MANUFACTURE

Title (de)
DÜNNFILMTRANSISTOREN UND IHRE HERSTELLUNG

Title (fr)
TRANSISTORS FILM MINCE ET LEUR FABRICATION

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Application
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Abstract (en)
[origin: WO0011709A1] In an insulated-gate top-gate thin film transistor, the insulated gate structure comprises a first gate insulator layer over the semiconductor body of the transistor, an intermediate conductive layer over the first gate insulator layer, a second gate insulator layer over the intermediate conductive layer and a gate conductor over the second gate insulating layer. The intermediate conductive layer enables the two insulator layers to be etched under separate conditions, and also acts as a field plate to reduce the effect of negative undercut in the top insulator layer.

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